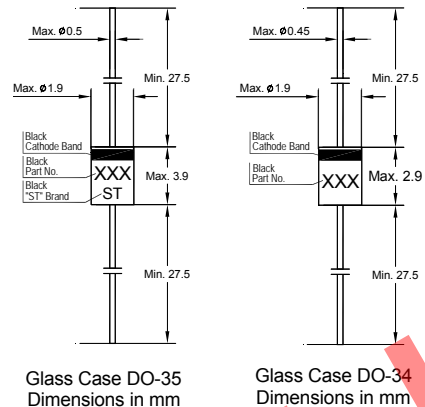


1N4149...1N4454

Silicon Epitaxial Planar Switching Diode

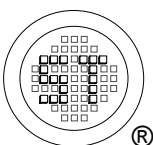
for general purpose and switching



Absolute Maximum Ratings and Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified.)

Type	Peak Reverse Voltage	Max. Average Rectified Current	Max. Power Dissipation at 25 °C	Max. Junction Temp.	Max. Forward Voltage		Max. Reverse Current		Max. Reverse Recovery Time	
	V_{RM} (V)	$I_{F(AV)}$ (mA)	P_{tot} (mW) ²⁾	T_j (°C)	V_F (V)	at I_F (mA)	I_R (nA)	at V_R (V)	t_{rr} (ns)	Conditions
1N4149 ¹⁾	100	150	500	200	1	10	25	20	4	$I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\ \Omega$, to $I_R = 1\text{ mA}$
1N4151	75	150	500	200	1	50	50	50	2	$I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\ \Omega$, to $I_R = 1\text{ mA}$
1N4152	40	150	400	175	0.55	0.1	50	30	2	$I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\ \Omega$, to $I_R = 1\text{ mA}$
1N4154	35	150	500	200	1	30	100	25	2	$I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\ \Omega$, to $I_R = 1\text{ mA}$
1N4447 ¹⁾	100	150	500	200	1	20	25	20	4	$I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\ \Omega$, to $I_R = 1\text{ mA}$
1N4449 ¹⁾	100	150	500	200	1	30	25	20	4	$I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\ \Omega$, to $I_R = 1\text{ mA}$
1N4450	40	150	400	175	0.54	0.5	50	30	4	$I_F = I_R = 10\text{ mA}$, to $I_R = 1\text{ mA}$
1N4451	40	150	400	175	0.5	0.1	50	30	10	$I_F = I_R = 10\text{ mA}$, to $I_R = 1\text{ mA}$
1N4453	30	150	400	175	0.55	0.01	50	20	-	-
1N4454	75	150	400	175	1	10	100	50	4	$I_F = I_R = 10\text{ mA}$, to $I_R = 1\text{ mA}$

¹⁾ These diodes are also available in glass case DO-34. Parameter for diodes in case DO-34: $P_{tot} = 300\text{ mW}$, $T_j = 175^\circ\text{C}$
²⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.



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